

WHAT IS CLAIMED IS:

1. An active matrix substrate, comprising:
  - a substrate body including a plurality of data lines and a plurality of scanning lines provided so as to cross each other;
  - a plurality of thin-film transistors electrically connected to the data lines and the scanning lines;
  - a plurality of pixel electrodes electrically connected to the plurality of thin-film transistors, respectively; and
  - an interlayer insulating film;
  - the thin-film transistors and the scanning lines constituting gate electrodes, the gate electrodes being formed in separate layers, and electrically connected via contact holes penetrating the interlayer insulating film between the gate electrodes and the scanning lines; and
  - the scanning lines constituting a layer positioned above a layer constituted by the data lines but under a layer constituted by the pixel electrodes, and a pattern of the scanning lines, a pattern of the data lines and a pattern of the pixel electrodes being partly overlapped in a top plan view.
2. The active matrix substrate according to Claim 1, the scanning lines being formed of a material including a metal.
3. The active matrix substrate according to Claim 1, the data lines being formed of a material including a metal.
4. The active matrix substrate according to Claim 1, the gate electrodes being formed of polycrystalline silicon.
5. The active matrix substrate according to Claim 1, further including a light shielding film extending in a matrix pattern in the directions along the scanning lines and the data lines, through the intermediary of an interlayer insulating film, below a semiconductor layer constituting channel regions of the thin-film transistors.
6. The active matrix substrate according to Claim 1, further including a storage capacitor electrode to form a storage capacitor between itself and the semiconductor layer constituting the channel regions of the thin-film transistors, and the storage capacitor electrode being formed of the same layer as the layer constituting the gate electrode.
7. The active matrix substrate according to Claim 6, the storage capacitor electrode and the light shielding film being electrically connected via a contact hole

penetrating an interlayer insulating film between the storage capacitor electrode and the light shielding film.

8. The active matrix substrate according to Claim 1, the scanning lines having portions that protrude along the data lines from trunks of the scanning lines.

9. The active matrix substrate according to Claim 1, the data lines having portions that protrude along the scanning lines from trunks of the data lines.

10. The active matrix substrate according to Claim 1, further including a relaying conductive film formed of the same layer as the layer constituting the data lines, and the semiconductor layer and the pixel electrodes being electrically connected through the relaying conductive film.

11. The active matrix substrate according to Claim 10, the pixel electrodes being formed of a transparent conductive film, and at least the upper surface of the relaying conductive film being formed of a material for ohmic junction with the transparent conductive film.

12. The active matrix substrate according to Claim 1, further including a drive circuit to drive the scanning lines or the data lines, and a gate line for a thin-film transistor constituting the drive circuit being formed by using the layer constituting the scanning lines, the layer constituting the data lines, or the layer constituting the gate electrodes.

13. The active matrix substrate according to Claim 1, the upper surface of a region where the scanning lines or the data lines are formed being positioned at a higher level than the upper surface of a central portion of a region wherein the pixel electrodes are formed.

14. The active matrix substrate according to Claim 1, an upper surface of the interlayer insulating film in contact, at the bottom side of the data lines, with the data lines being planarized.

15. The active matrix substrate according to Claim 1, an upper surface of the interlayer insulating film in contact, at the bottom side of the scanning lines, with the scanning lines being planarized.

16. The active matrix substrate according to Claim 1, further including a recessed portion in the region of the substrate body where the thin-film transistors are formed.

17. An electro-optical device, comprising:  
the active matrix substrate according to Claim 1.

18. An electronic equipment, comprising:  
the electro-optical device according to Claim 17.